

Title (en)
NITRIDE BONDING LAYER.

Title (de)
NITRID-VERBINDUNGSSCHICHT.

Title (fr)
COUCHE DE LIAISON DE NITRURE.

Publication
EP 0177562 A4 19870603 (EN)

Application
EP 85901781 A 19850319

Priority
US 59215284 A 19840322

Abstract (en)
[origin: WO8504519A1] An integrated circuit chip includes a layer of silicon nitride (4-20) deposited above the upper metallization and silicon oxide intermetallic dielectric (4-10), above which a layer of polyimide (4-50) supports a network of electrical leads; the layer of nitride (4-20) extending completely over the silicon oxide (4-10) from the streets (4-200) at the edge of the die to overlap metallic contacts (4-05) connected from the metallization layer to the upper electrical leads.

IPC 1-7
H01L 23/30; **H01L 23/50**; **H01L 21/318**; **H01L 21/312**

IPC 8 full level
H01L 21/312 (2006.01); **H01L 21/318** (2006.01); **H01L 23/532** (2006.01)

CPC (source: EP KR)
H01L 23/29 (2013.01 - KR); **H01L 23/5329** (2013.01 - EP); **H01L 2924/0002** (2013.01 - EP)

Citation (search report)
• [X] DE 3116406 A1 19820616 - HITACHI LTD [JP]
• See references of WO 8504519A1

Designated contracting state (EPC)
DE FR GB NL

DOCDB simple family (publication)
WO 8504519 A1 19851010; EP 0177562 A1 19860416; EP 0177562 A4 19870603; JP S61501537 A 19860724; KR 860700075 A 19860131

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US 8500454 W 19850319; EP 85901781 A 19850319; JP 50141885 A 19850319; KR 850700325 A 19851121